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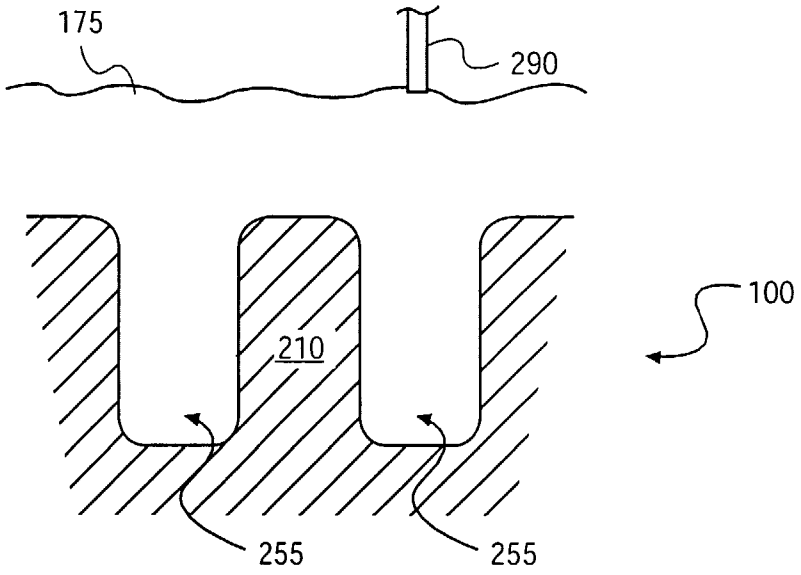
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(54) Title: MATERIAL DEPOSITION FROM A LIQUEFIED GAS SOLUTION



(57) Abstract: Introduction of a liquefied gas solution for deposition of a material on a semiconductor substrate. The substrate can have a trench etched thereinto with the solution including ions of the material to be deposited in the trench. The substrate can have a barrier layer at its surface prior to introduction of a liquefied gas solution including ions of a metal to be deposited above the barrier. A material layer to be formed on the substrate can be a tantalum barrier, a copper layer or other semiconductor processing feature.

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